

20V P-Channel Enhancement-Mode MOSFET

FEATURES

- $R_{DS(ON)} \leq 110\text{m}\Omega @ V_{GS}=-4.5\text{V}$
- $R_{DS(ON)} \leq 150\text{m}\Omega @ V_{GS}=-2.5\text{V}$
- Super high density cell design for extremely low $R_{DS(ON)}$
- S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

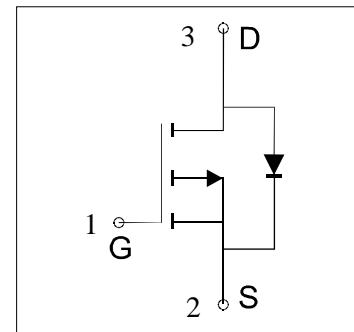
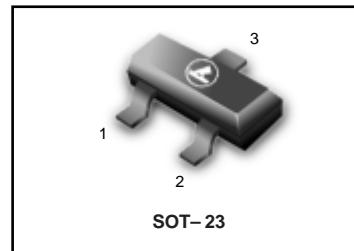
APPLICATIONS

- Power Management in Note book
- Portable Equipment
- Battery Powered System
- Load Switch
- DSC
- We declare that the material of product are Halogen Free and compliance with RoHS requirements.

Ordering Information

Device	Marking	Shipping
LP2301ALT1G S-LP2301ALT1G	01A	3000/Tape&Reel
LP2301ALT3G S-LP2301ALT3G	01A	10000/Tape&Reel

**LP2301ALT1G
S-LP2301ALT1G**



Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ Unless Otherwise Noted)

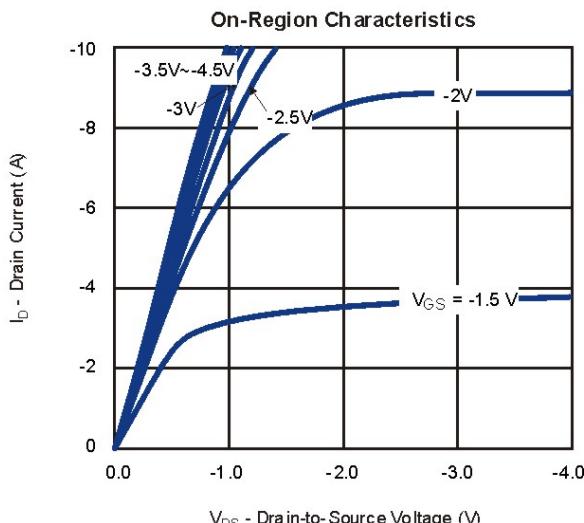
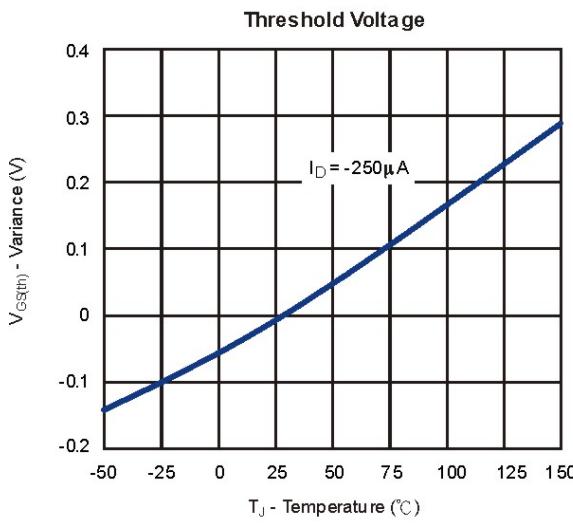
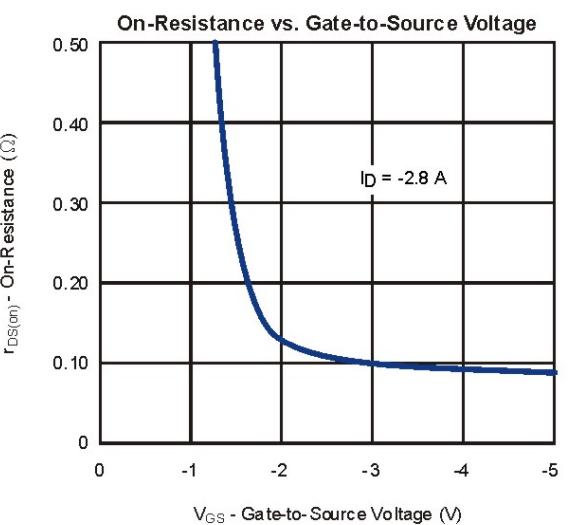
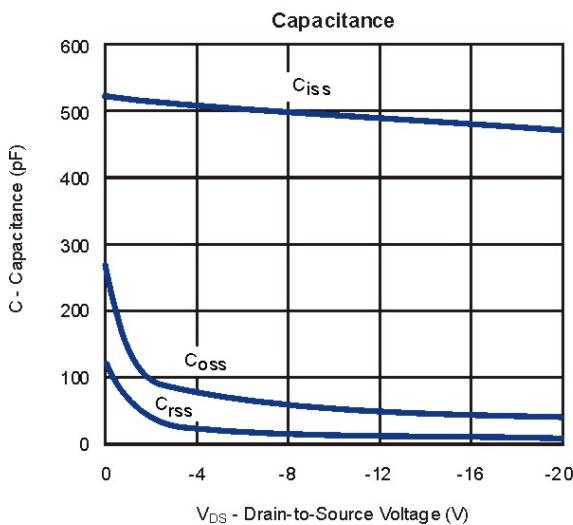
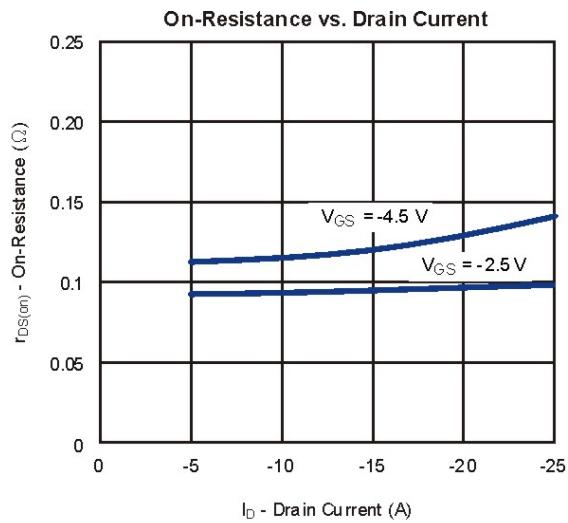
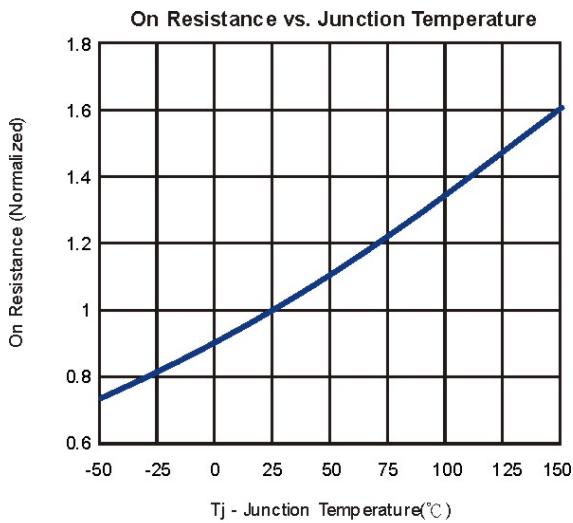
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DSS}	-20	V
Gate-Source Voltage	V_{GSS}	± 8	V
Continuous Drain Current ($T_j=150^\circ\text{C}$)*	I_D	-2.0	A
		-1.6	
Pulsed Drain Current	I_{DM}	-10	A
Maximum Power Dissipation	P_D	0.7	W
		0.45	
Operating Junction Temperature	T_J	-55 to 150	°C
Storage Temperature Range	T_{STG}	-55 to 150	°C
Thermal Resistance-Junction to Ambient*	$R_{\theta JA}$	Typical	°C/W
		100	
		Maximum	
		175	

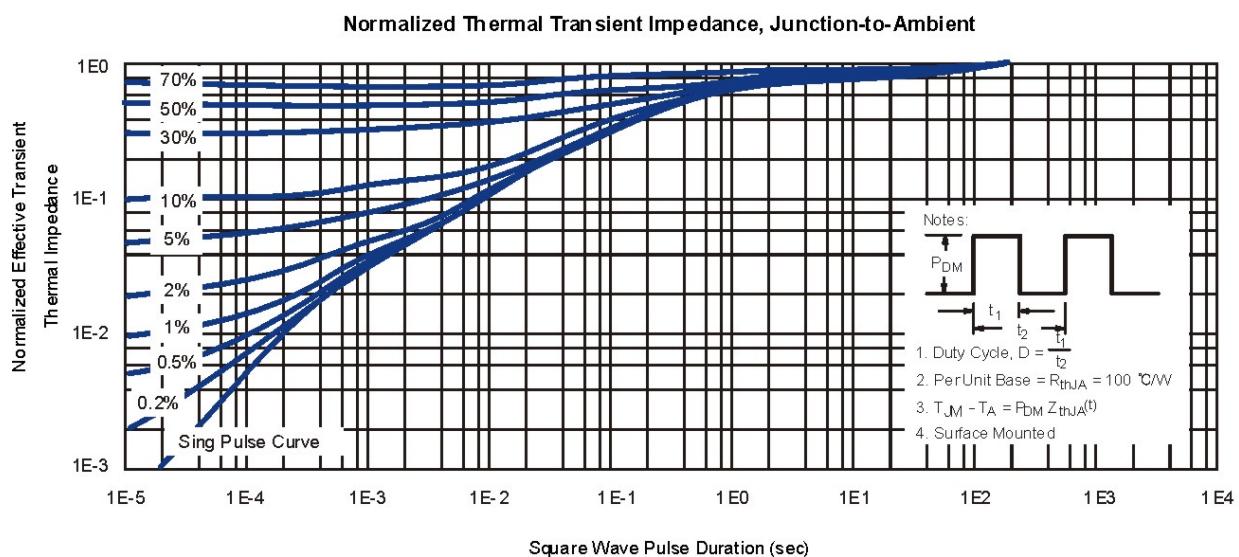
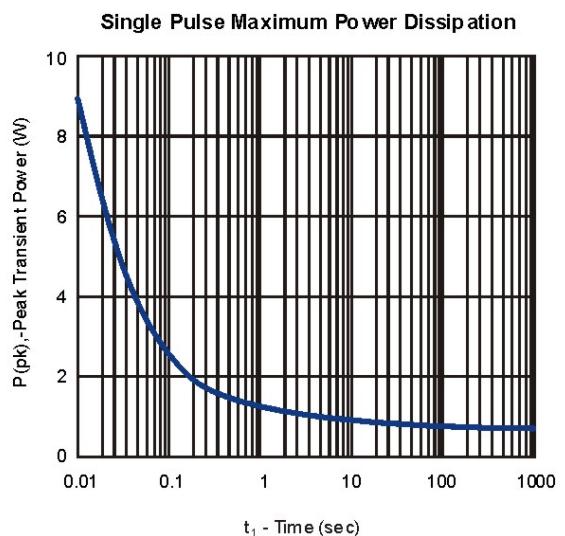
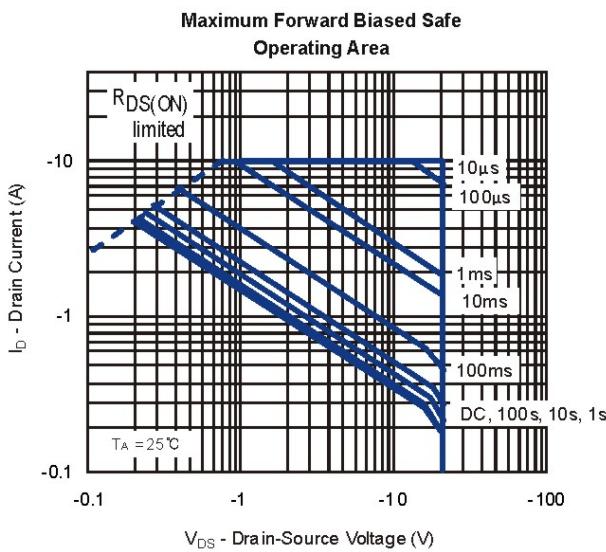
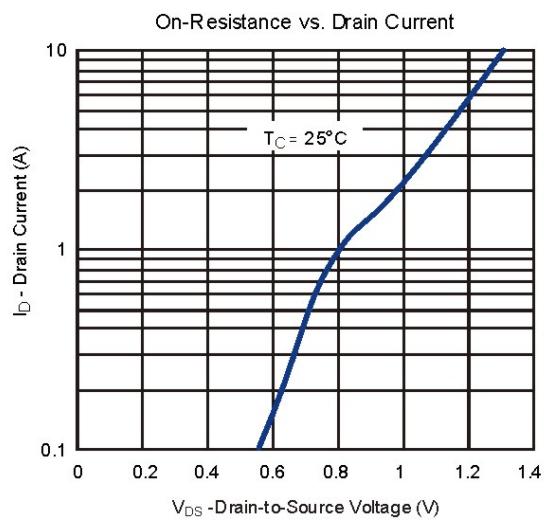
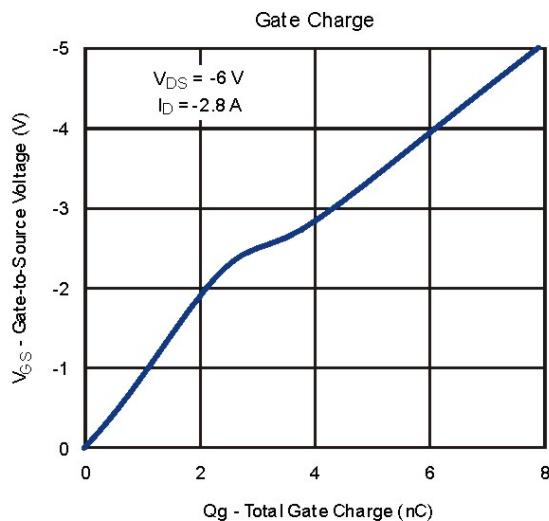
* The device mounted on 1in² FR4 board with 2 oz copper

LP2301ALT1G , S-LP2301ALT1G
ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Limit	Min	Typ	Max	Unit
STATIC						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250 μ A	-20			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250 μ A	-0.4	-0.6	-1	V
I _{GSS}	Gate Leakage Current	V _{DS} =0V, V _{GS} =±8V			±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-20V, V _{GS} =0V			-1	μ A
R _{Ds(ON)}	Drain-Source On-Resistance ^a	V _{GS} =-4.5V, I _D = -2.8A		90	110	m Ω
		V _{GS} =-2.5V, I _D = -2.0A		110	150	
V _{SD}	Diode Forward Voltage	I _S =-1A, V _{GS} =0V		-0.7	-1.4	V
DYNAMIC						
Q _g	Total Gate Charge	V _{DS} =-6V, V _{GS} =-4.5V, I _D =-2.8A		7.2		nC
Q _{gs}	Gate-Source Charge			2.2		
Q _{gd}	Gate-Drain Charge			1.2		
R _g	Gate resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz		7.5		Ω
C _{iss}	Input Capacitance	V _{DS} =-15V, V _{GS} =0V, f=1MHz		480		pF
C _{oss}	Output Capacitance			46		
C _{rss}	Reverse Transfer Capacitance			10		
t _{d(on)}	Turn-On Delay Time	V _{DS} =-6V, R _L =6 Ω R _{GEN} =6 Ω , V _{GS} =-4.5V		50		ns
t _r	Turn-On Rise Time			30		
t _{d(off)}	Turn-Off Delay Time			40		
t _f	Turn-Off Fall time			11		

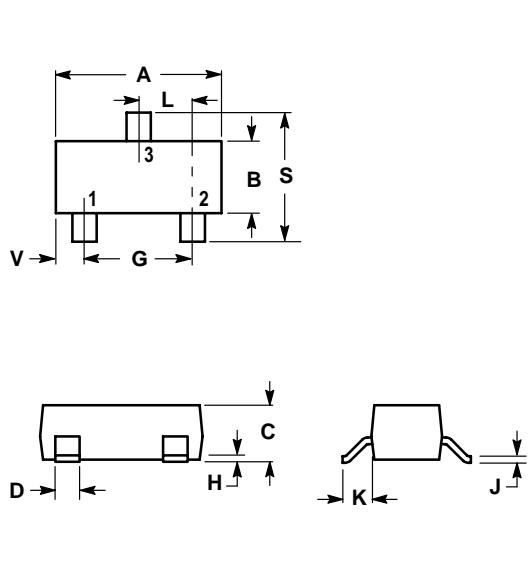
Notes: a. Pulse test; pulse width \leq 300us, duty cycle \leq 2%

Typical Characteristics (T_J = 25°C Noted)
LP2301ALT1G , S-LP2301ALT1G


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Notes:

- 1. Duty Cycle, $D = \frac{t_1}{t_2}$
- 2. Per Unit Base = $R_{thJA} = 100\text{ }^\circ\text{C/W}$
- 3. $T_{JM} - T_A = P_{DM} Z_{thJA}(t)$
- 4. Surface Mounted

LP2301ALT1G , S-LP2301ALT1G
SOT-23

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M,1982
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

